

1 ABSTRACT OF THE DISCLOSURE

2 The invention encompasses a method of removing at least some of
3 a material from a semiconductor substrate. A feed gas is fed through
4 an ozone generator to generate ozone. The feed gas comprises at least
5 99.999% O₂ (by volume). The ozone, or a fragment of the ozone, is
6 contacted with a material on a semiconductor substrate to remove at
7 least some of the material from the semiconductor substrate. The
8 invention also encompasses another method of removing at least some of
9 a material from a semiconductor substrate. A mixture of ozone and
10 organic solvent vapors is formed in a reaction chamber. At least some
11 of the ozone and solvent vapors are contacted with a material on a
12 semiconductor substrate to remove at least some of the material from
13 the semiconductor substrate.
14
15
16
17
18
19
20
21
22
23